



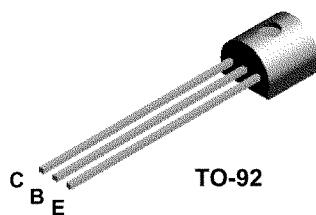
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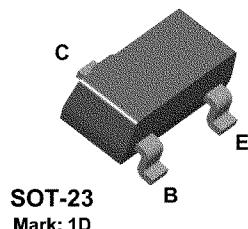
FLAT P, 3/F, EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.
TEL: 2790-0314 FAX: 2790-0206

FAIRCHILD
SEMICONDUCTOR™

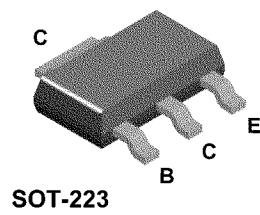
MPSA42



MMBTA42



PZTA42



MPSA42 / MMBTA42 / PZTA42

NPN High Voltage Amplifier

This device is designed for application as a video output to drive color CRT and other high voltage applications. Sourced from Process 48.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	300	V
V_{CBO}	Collector-Base Voltage	300	V
V_{EBO}	Emitter-Base Voltage	6.0	V
I_C	Collector Current - Continuous	500	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max			Units
		MPSA42	*MMBTA42	**PZTA42	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	1,000 8.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

* Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06".

** Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².



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(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	300		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, I_E = 0$	300		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100 \mu\text{A}, I_C = 0$	6.0		V
I_{CBO}	Collector-Cutoff Current	$V_{CB} = 200 \text{ V}, I_E = 0$		0.1	μA
I_{EBO}	Emitter-Cutoff Current	$V_{EB} = 6.0 \text{ V}, I_C = 0$		0.1	μA

ON CHARACTERISTICS*

h_{FE}	DC Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_C = 30 \text{ mA}, V_{CE} = 10 \text{ V}$	25	40	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 20 \text{ mA}, I_B = 2.0 \text{ mA}$		0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 20 \text{ mA}, I_B = 2.0 \text{ mA}$		0.9	V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V}, f = 100 \text{ MHz}$	50		MHz
C_{cb}	Collector-Base Capacitance	$V_{CB} = 20 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		3.0	pF

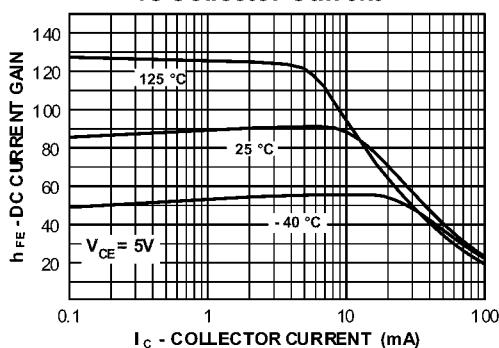
*Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$

Spice Model

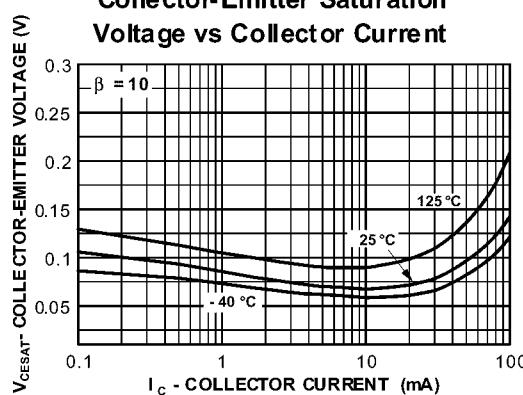
NPN ($I_S=34.9f$ $X_{Ti}=3$ $E_g=1.11$ $V_{af}=100$ $B_f=2.65K$ $N_e=1.708$ $I_{se}=16.32p$ $I_{kf}=23.79m$ $X_{tb}=1.5$ $B_r=9.769$ $N_c=2$ $I_{sc}=0$ $I_{kr}=0$ $R_c=7$ $C_{jc}=14.23p$ $M_{jc}=.5489$ $V_{jc}=.75$ $F_c=.5$ $C_{je}=49.62p$ $M_{je}=.4136$ $V_{je}=.75$ $T_r=934.3p$ $T_f=1.69n$ $I_{tf}=5$ $V_{tf}=20$ $X_{tf}=150$ $R_b=10$)

Typical Characteristics

DC Current Gain
vs Collector Current



Collector-Emitter Saturation Voltage vs Collector Current





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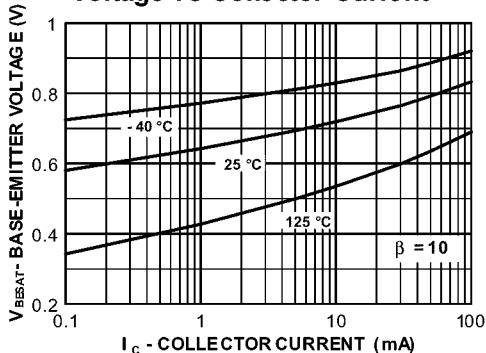
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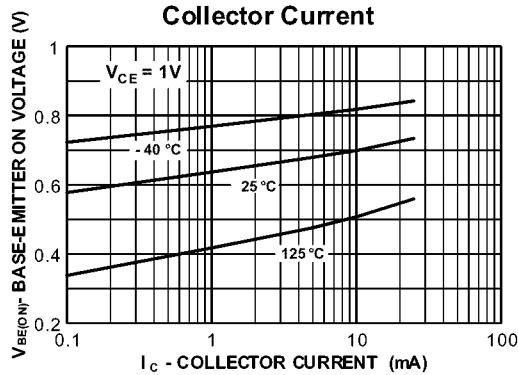
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Typical Characteristics (continued)

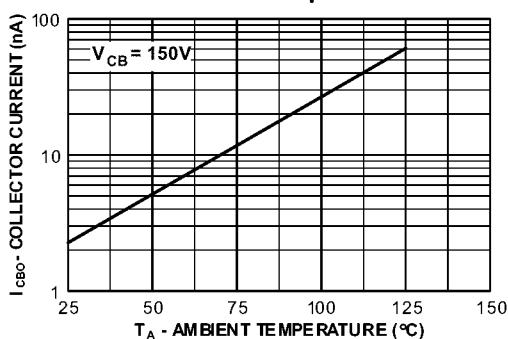
Base-Emitter Saturation Voltage vs Collector Current



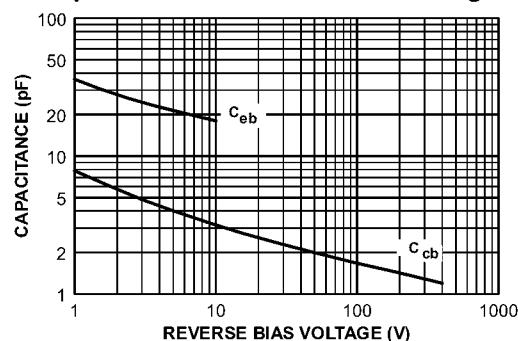
Base-Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature



Collector-Base and Emitter-Base Capacitance vs Reverse Bias Voltage



Power Dissipation vs Ambient Temperature

